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1 and (nitride near buffer)

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	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
25	<input type="checkbox"/> US 20030019993 A1	20030116	15	NITRISE SEMICONDUCTOR DEVICE	257/99	257/E33.028; 257/E33.03
26	<input type="checkbox"/> US 20030006418 A1	20030109	13	Group III nitride based light emitting diode structures with a quantum well and superlattice, grown III nitride based quantum well structures and Method for growing high quality group-III nitride thin film by metal organic chemical vapor deposition	257/79	257/E33.008
27	<input type="checkbox"/> US 20020192373 A1	20021219	7	Method for growing high quality group-III nitride thin film by metal organic chemical vapor deposition	427/255.28	
28	<input type="checkbox"/> US 20020179911 A1	20021205	11	Pseudosubstrate gallium nitride semiconductor layers on silicon carbide substrates	257/77	257/615; 257/622; 257/628
29	<input type="checkbox"/> US 20020148534 A2	20021017	13	METHODS OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS BY LATERAL OVERGROWTH THROUGH OFFSET MASKS	148/33	117/104; 257/E21.125; 438/Q31
30	<input type="checkbox"/> US 20020125491 A1	20020912	6	Semiconductor element	257/54	257/96; 257/E21.127
31	<input type="checkbox"/> US 20020111044 A1	20020815	13	Gallium nitride semiconductor structures fabricated by pseudosubstrate methods of fabricating gallium nitride semiconductor layers on weak masks	438/797	257/E21.127; 257/E21.131
32	<input type="checkbox"/> US 20020110997 A1	20020815	9	Methods of fabricating gallium nitride semiconductor layers on substrates including non-gallium nitride masks	438/479	257/E21.125; 257/E21.127;
33	<input type="checkbox"/> US 20020100412 A1	20020801	32	Low dislocation buffer and process for production thereof as well as device provided with low dislocation buffer	117/69	257/E21.131
34	<input type="checkbox"/> US 20020098693 A1	20020725	24	Single step pseudosubstrate lateral epitaxial overgrowth of group III-nitride epilayer with non-III-nitride buffer layer and resultant structure	438/687	257/E21.112; 257/E21.131
35	<input type="checkbox"/> US 20020078881 A1	20020627	43	Method and apparatus for producing M'N columns and N'M'N materials grown thereon	117/64	257/E21.097